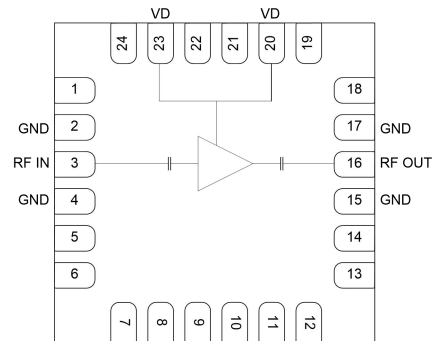


## GaAs MMIC Power Amplifier Chip, 4-8 GHz

### Performance characteristics

- Frequency range: 4 - 8 GHz
- Small signal gain: 18.5dB
- Gain Flatness:  $\pm 1.0$ dB
- Noise figure: 6.5dB
- P -1 dB : 22dBm
- Psat: 23dBm
- Power supply: +5 V /175 mA
- 50Ohm input / output
- Chip size: QFN 4X4

### Block Diagram



### Product Introduction

GPA-0408B-CQ4 is a broadband low noise amplifier chip with a frequency range of 4GHz~8GHz, a small signal gain of 18.5dB, and a P-1 output of 22dBm. GPA-0408B-CQ4 is powered by a single +5V power supply. This chip uses a 4 x 4 mm ceramic surface mount package to achieve airtight packaging. The surface of the pin pad is gold-plated and is suitable for reflow soldering installation.

### Using the Limit Parameter

Maximum drain voltage	+7V
Maximum input power	+20dBm
Operating temperature	-55 ~ +85°C
Storage temperature	-65 ~ +150°C

Exceeding any of these maximum limits may cause permanent damage.

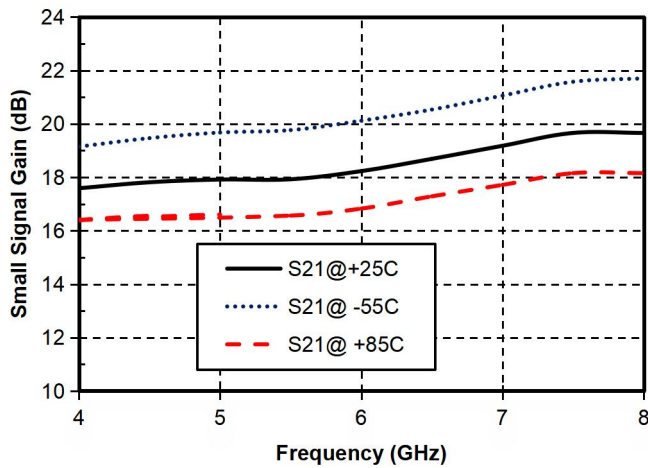
### Electrical performance parameters ( TA = +25°C , Vd=+5V )

Index	Minimum	Typical Value	Maximum	Unit
Frequency Range	4-8			GHz
Small Signal Gain	7.5	18.5	-	dB
Gain Flatness		$\pm 1.0$		dB
P -1dB	-	22	-	dBm
Psat	-	23	-	dBm
Input return loss	-	15	-	dB
Output return loss	-	15	-	dB
Quiescent Current		175		mA

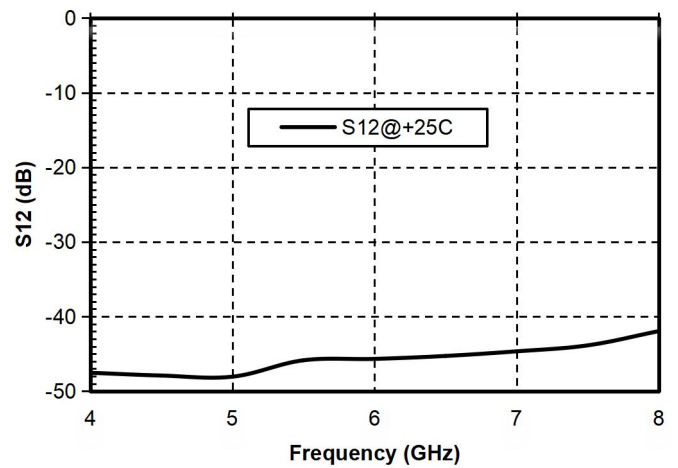
## GaAs MMIC Power Amplifier Chip, 4 - 8 GHz

Main index test curve

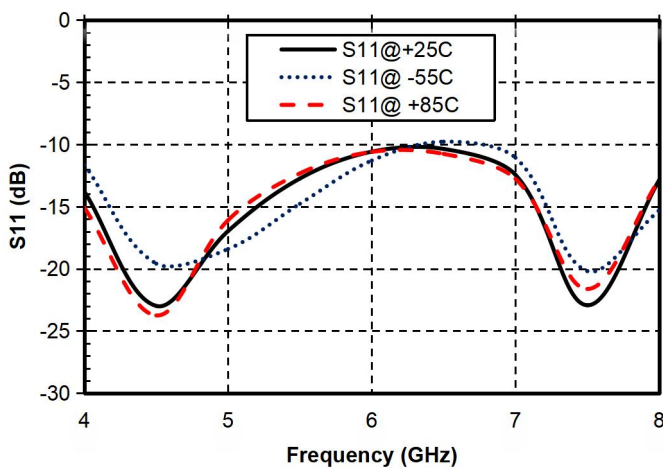
Gain vs. Frequency



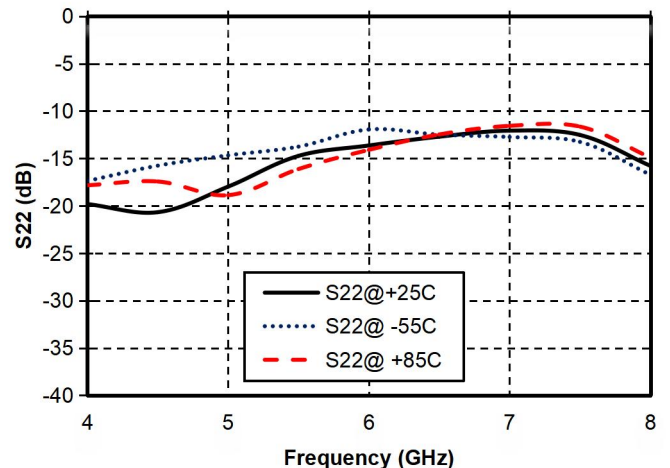
Reverse Isolation vs. Frequency



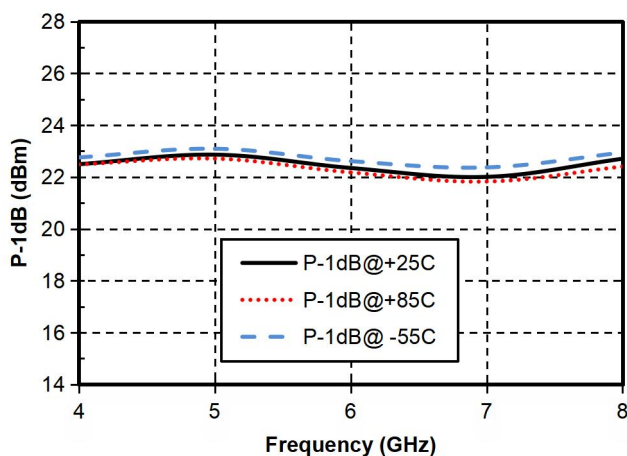
Input Return Loss vs. Frequency



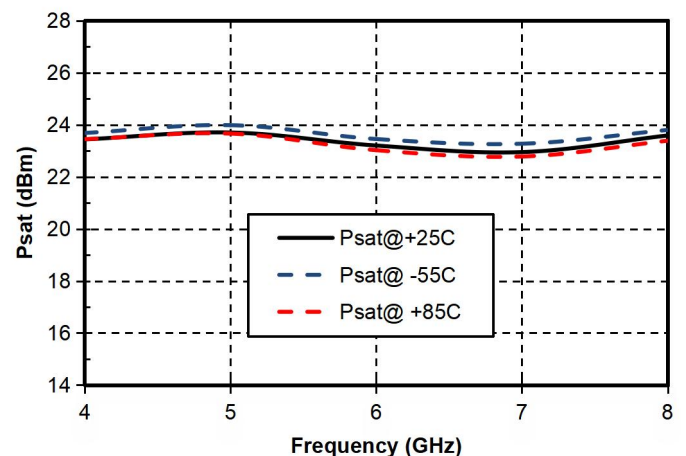
Output Return Loss vs. Frequency



P-1dB vs. Frequency

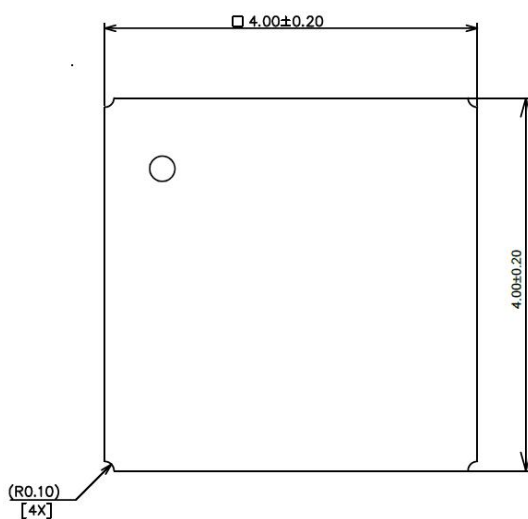


P sat vs. frequency

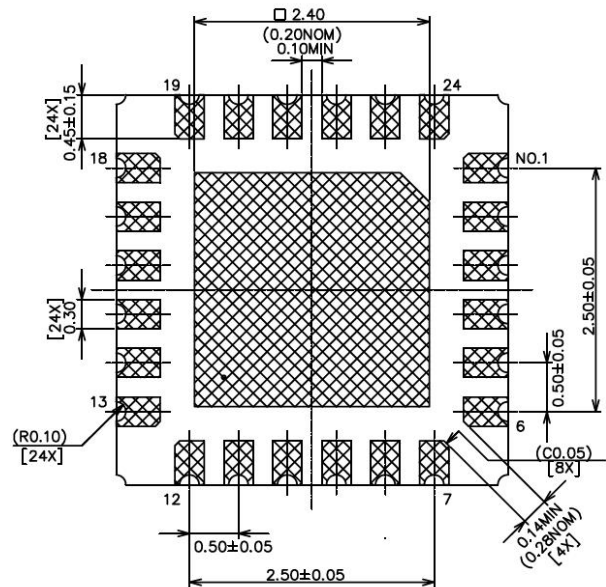


## GaAs MMIC Power Amplifier Chip, 4 - 8 GHz

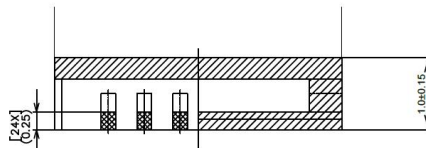
### Appearance structure



Top view



Bottom view



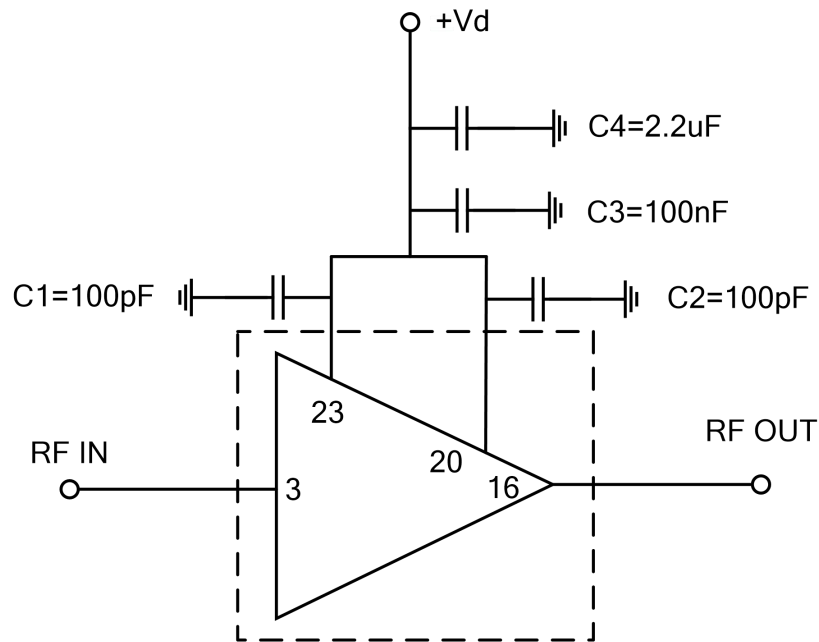
Side View

All units in the figures are millimeters .

Pin Definition		
Bonding point number	Function Symbol	Functional Description
3	RFIN	RF signal input terminal, no DC blocking capacitor required
16	RFOUT	RF signal output terminal, no DC blocking capacitor required
20, 23	VDD	Amplifier Drain Bias
2, 4, 15, 17	GND	The bottom of the chip needs to be well grounded to RF and DC
1, 5~14, 18, 19, 21, 22, 24	NC	No welding required

## GaAs MMIC Power Amplifier Chip, 4 - 8 GHz

### Recommended Circuit



Raw material	Capacitance, inductance, resistance
C1	100pF
C 2	100 pF
C 3	100nF
C 4	2.2uF

### Precautions for use

- Sealing material: Ceramic material that meets ROHS standards
- Lead frame material: copper alloy
- Lead surface plating: gold, gold layer thickness greater than 1.3um
- Maximum reflow peak temperature: 260 °C